



## Clean Version of Amended Claims

1           6.     A method for cleaning a metal contact region of a semiconductor  
2     substrate, comprising exposing the metal contact region to hydrofluoric acid  
3 *A3*     vapor and water vapor in a process chamber held at temperature and  
4     pressure conditions that are controlled to form on the substrate no more than  
5     a sub-monolayer of reactants and products produced by the vapor as the  
6     metal contact region is cleaned by the vapor.

---

1           9.     The method of either of claims 7 or 8 wherein the process  
2     chamber temperature and pressure conditions are controlled to form on the  
3     substrate no more than a saturated monolayer of etch reactants and products  
4 *A4*     produced by the vapor as the oxide is etched by the vapor.

---

1           10.    The method of either of claims 7 or 8 wherein the process  
2     chamber temperature and pressure conditions are controlled to form on the  
3     substrate no more than a sub-monolayer of etch reactants and products  
4     produced by the vapor as the oxide is etched by the vapor.

---

1           15.    The method of any of claims 12, 13, or 14 wherein the process  
2 *A5*     chamber temperature and pressure conditions are controlled to form on the  
3     substrate no more than a sub-monolayer of etch reactants and products  
4     produced by the vapor as the oxide is etched by the vapor.

---

1           23.    The method of claim 22 wherein the process chamber  
2 *A6*     temperature and pressure conditions are controlled to form on the substrate  
3     no more than a saturated monolayer of etch reactants and products produced  
4     by the vapor as the oxide is etched by the vapor.

Alb  
Cont

1           24.    The method of claim 22 wherein the process chamber  
2           temperature and pressure conditions are controlled to form on the substrate  
3           no more than a sub-monolayer of etch reactants and products produced by  
4           the vapor as the oxide is etched by the vapor.

---